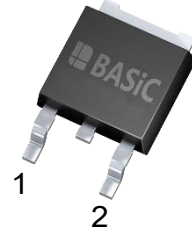


$V_{RRM}$  = 650 V  
 $I_F (T_C=155^\circ\text{C})$  = 6 A  
 $Q_C$  = 17 nC

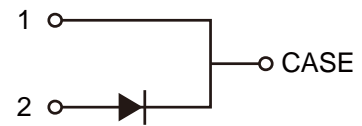
TO-252-2

CASE



### Features

- Extremely low reverse current
- No reverse recovery current
- Temperature independent switching
- Positive temperature coefficient on  $V_F$
- Excellent surge current capability
- Low capacitive charge



### Benefits

- Essentially no switching losses
- System efficiency improvement over Si diodes
- Increased power density
- Enabling higher switching frequency
- Reduction of heat sink requirements
- System cost savings due to smaller magnetics
- Reduced EMI



### Applications

- Switch mode power supplies (SMPS)
- Uninterruptible power supplies
- Motor drivers
- Power factor correction

### Package Pin Definitions

- Pin1- Cathode
- Pin2- Anode

### Package Parameters

Part Number	Marking	Package
B1D06065E	B1D06065E	TO-252-2

**Maximum Ratings ( $T_c=25^\circ\text{C}$  unless otherwise specified)**

Symbol	Parameter	Test conditions	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		650	V
$V_{RSM}$	Non-repetitive peak reverse voltage		650	V
$I_F$	Continuous forward current	$T_c=25^\circ\text{C}$ $T_c=155^\circ\text{C}$	19 6	A
$I_{FSM}$	Non-repetitive forward surge current	$T_c=25^\circ\text{C}$ , $t_p=10\text{ms}$ , Half Sine Wave	45	A
$\int i^2 dt$	$i^2t$ value	$T_c=25^\circ\text{C}$ , $t_p=10\text{ms}$	10.12	A <sup>2</sup> S
$P_{tot}$	Power dissipation	$T_c=25^\circ\text{C}$ $T_c=110^\circ\text{C}$	75 32	W
$T_j$	Operating junction temperature		-55~175	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~175	$^\circ\text{C}$

**Thermal Characteristics**

Symbol	Parameter	Value			Unit
		Min.	Typ.	Max.	
$R_{th(jc)}$	Thermal resistance from junction to case		1.983		K/W

**Electrical Characteristics**
**Static Characteristics**

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$V_{DC}$	DC blocking voltage	$T_j=25^{\circ}C$	650			V
$V_F$	Diode forward voltage	$I_F=6A$ $T_j=25^{\circ}C$ $I_F=6A$ $T_j=175^{\circ}C$		1.43 1.73	1.60 2.20	V
$I_R$	Reverse current	$V_R=650V$ $T_j=25^{\circ}C$ $V_R=650V$ $T_j=175^{\circ}C$		1 20	60 200	$\mu A$

**AC Characteristics**

Symbol	Parameter	Test conditions	Value			Unit
			Min.	Typ.	Max.	
$Q_C$	Total capacitive charge	$V_R=400V$ $T_j=25^{\circ}C$ $Q_c = \int_0^{V_R} C(V)dV$		17		nC
$C$	Total capacitance	$V_R=1V$ $f=1MHz$ $V_R=300V$ $f=1MHz$ $V_R=600V$ $f=1MHz$		271 30.1 29.8		pF
$E_C$	Capacitance stored energy	$V_R=400V$		4.5		$\mu J$

Typical Performance

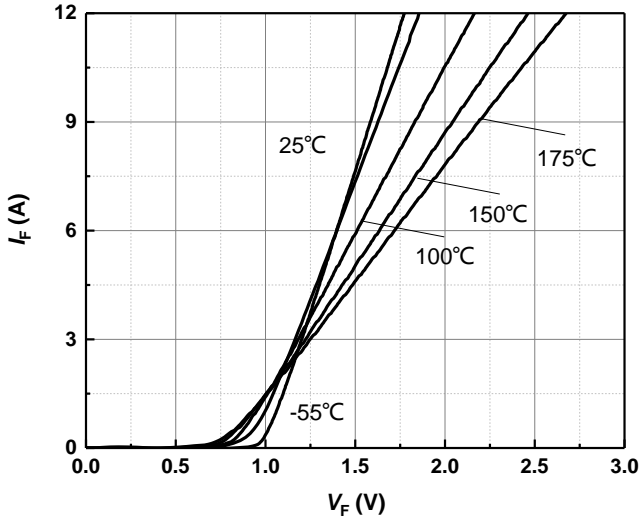


Figure 1. Typical forward characteristics

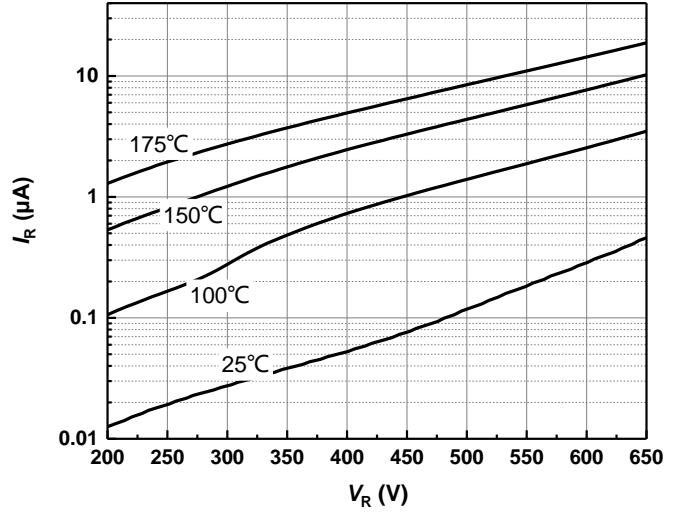


Figure 2. Typical reverse current as function of reverse voltage

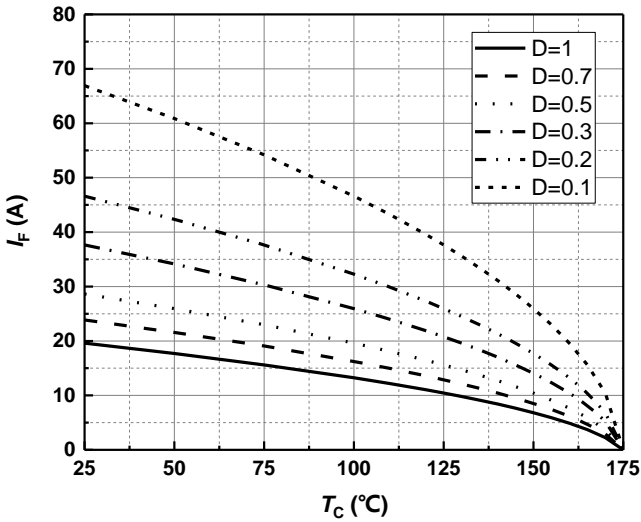


Figure 3. Diode forward current as function of temperature, D=duty cycle

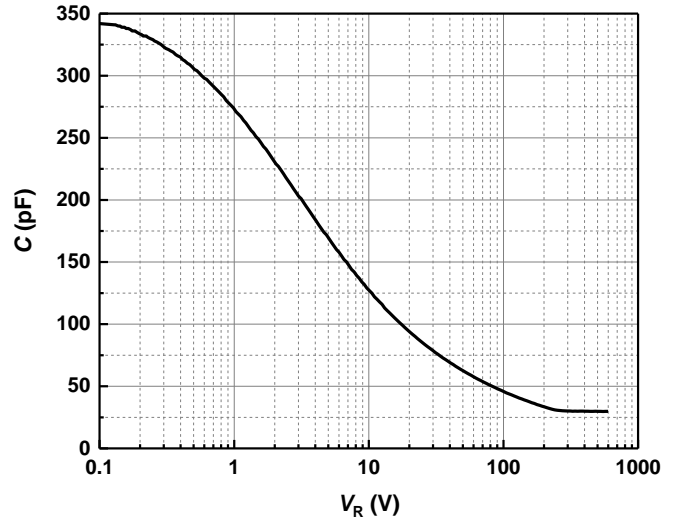
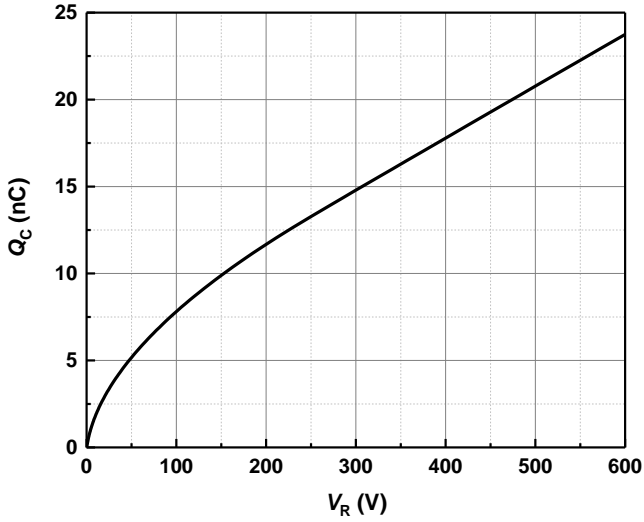
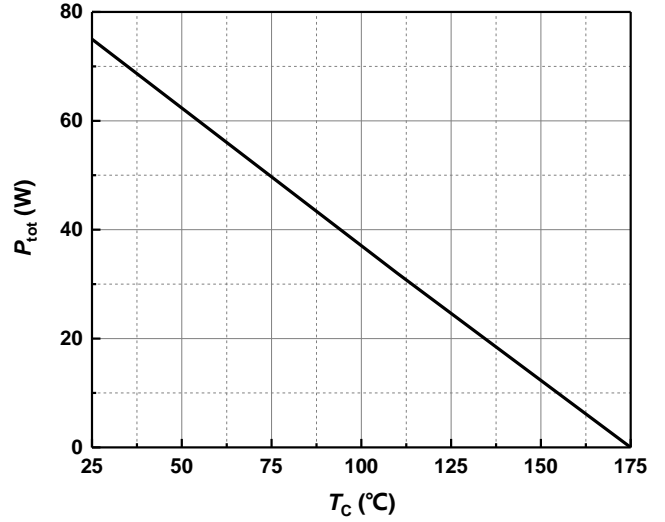


Figure 4. Typical capacitance as function of reverse voltage,  $C=f(V_R)$ ;  $T_J=25^\circ\text{C}$ ;  $f=1\text{ MHz}$

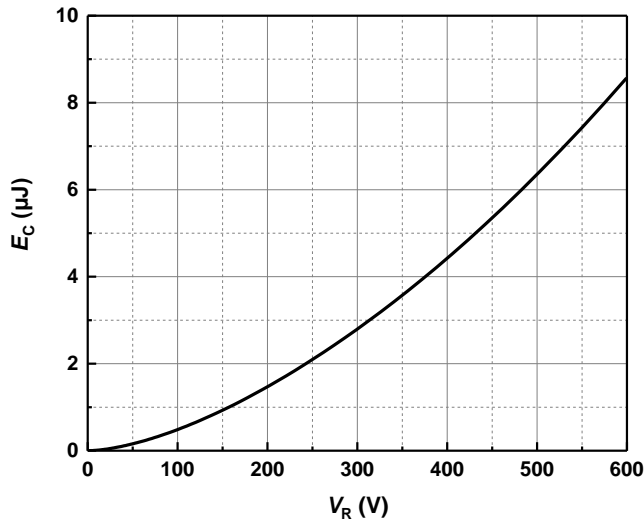
**Typical Performance**



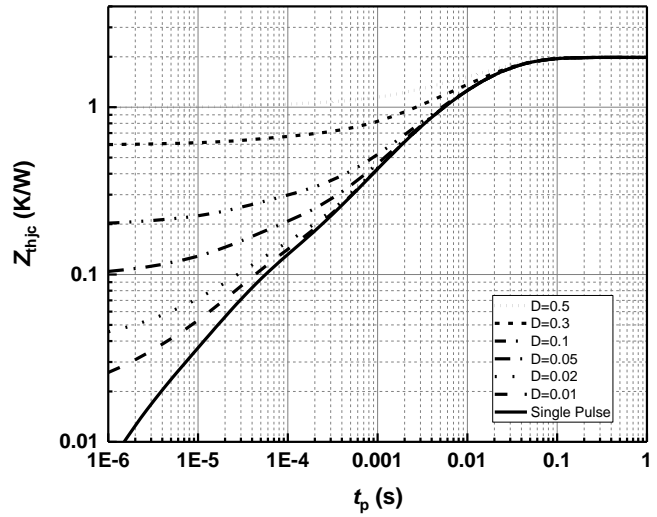
**Figure 5. Typical reverse charge as function of reverse voltage**



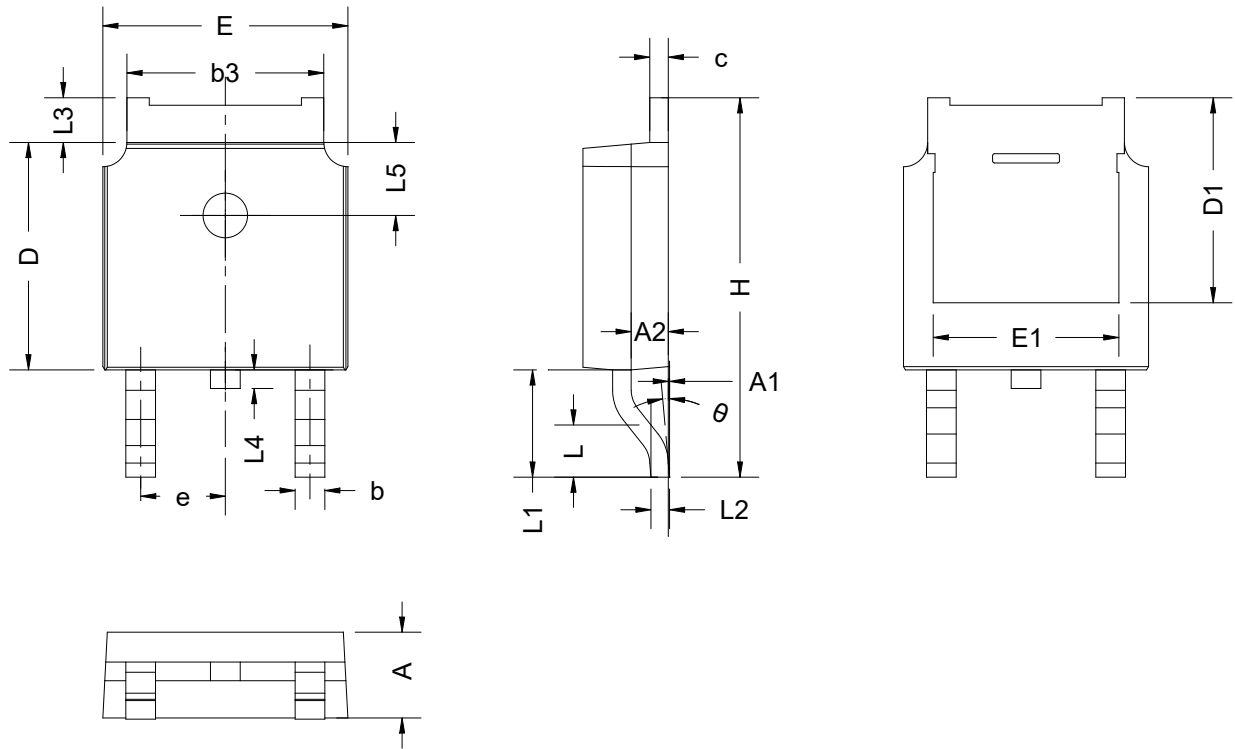
**Figure 6. Power dissipation as function of case temperature**



**Figure 7. Capacitance stored energy**



**Figure 8. Max. transient thermal impedance,  $Z_{thjc} = f(t)$ , parameter:  $D = t/T$**

**Package Dimensions**


SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.90	1.07	1.17
b	0.68	0.78	0.90
b3	5.23	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30 REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286 BSC		
H	9.40	10.10	10.50
L	1.38	1.50	1.75
L1	2.90 REF		
L2	0.51 BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
L5	1.65	1.80	1.95
$\theta$	0°	-	8°

## Revision History

Document Version	Date of Release	Description of Changes
Rev. 1.0	2020-05-30	Release of the datasheet.
Rev. 2.0	2020-07-06	Characteristics updated.
Rev. 2.1	2020-10-23	Maximum characteristics updated.
Rev. 2.2	2020-11-06	Characteristics updated.

**BASiC Semiconductor Ltd.**  
**Shenzhen, China**  
**© 2021 BASiC Semiconductor Ltd.**  
**All Rights Reserved.**

### Information

For further information on technology, delivery terms and conditions and prices, please contact the nearest BASiC Semiconductor Office

### Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, BASiC semiconductor Ltd. hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.